DATA SHEET

74HC1G126
74HCT1G126
Bus buffer/line driver; 3-state

Product specification
File under Integrated Circuits, IC06

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Philips
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Bus buffer/line driver; 3-state

74HC1G126
74HCT1G126

FEATURES

- Wide operating voltage : 2.0 to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Very small 5 pins package
- Output capability : bus driver

DESCRIPTION

The 74HC1G/HCT1G126 is a highspeed Si-gate CMOS device.

The 74HC1G/HCT1G126 provides one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (OE). A LOW at OE causes the output as assume a high impedance OFF-state.

The bus driver output currents are equal compared to the 74HC/HCT126.

FUNCTION TABLE

INPUTS		OUTPUT
OE	inA	outY
H	L	L
H	H	H
L	X	Z

H = HIGH voltage level

L = LOW voltage level

X = Don't care

Z = High impedance OFF state

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; $t_r = t_f \leq 6.0$ ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			HC1G	HCT1G	
t_{PHL}/ t_{PLH}	propagation delay inA to outY	C_L = 15 pF VCC = 5 V	9	10	ns
C_I	input capacitance		1.5	1.5	pF
C_{PD}	power dissipation capacitance	notes 1 and 2	30	27	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
   f_i = input frequency in MHz;
   f_o = output frequency in MHz;
   C_L = output load capacitance in pF;
   V_{CC} = supply voltage in V;
   $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.
2. For HC1G the condition is V_I = GND to V_{CC}.
   For HCT1G the condition is V_I = GND to VCC – 1.5 V.

PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
1, 2	OE, inA	output enable input, data input
3	GND	ground (0 V)
4	outY	data output
5	V_{CC}	positive supply voltage

ORDERING AND PACKAGE INFORMATION

OUTSIDE NORTH AMERICA	NORTH AMERICA	PACKAGES					
		TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74HC1G126GW		–40 °C to +125 °C	5	SC88A	plastic	SOT353	HN
74HCT1G126GW			5	SC88A	plastic	SOT353	TN

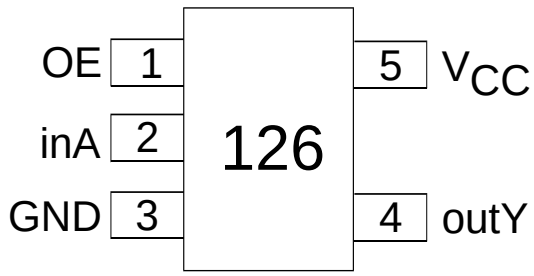


Fig.1 Pin configuration.

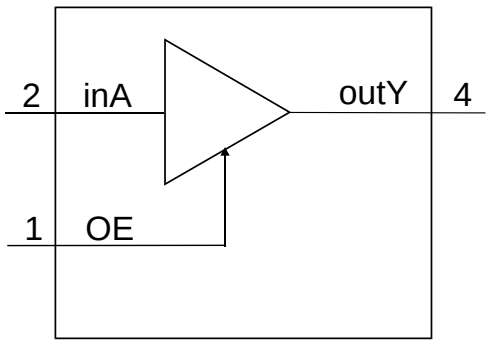


Fig.2 Logic symbol.

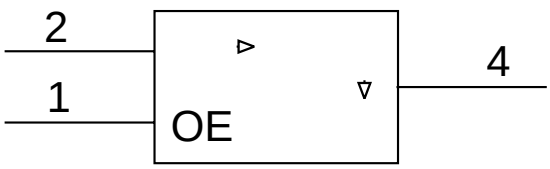


Fig.3 IEC logic symbol.

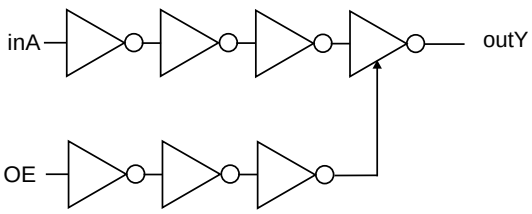


Fig.4 Logic diagram.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	74HC1G			74HCT1G			UNIT	CONDIITIONS
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
V_{CC}	DC supply voltage	2.0	5.0	6.0	4.5	5.0	5.5	V	
V_I	input voltage	0	–	V_{CC}	0	–	V_{CC}	V	
V_O	output voltage	0	–	V_{CC}	0	–	V_{CC}	V	
T_{amb}	operating ambient temperature range	–40	25	+125	–40	25	+125	°C	see DC and AC characteristics per device
t_r,t_f	input rise and fall times except for Schmitt-trigger inputs	–	–	1000	–	–	–	ns	V_{CC} = 2.0 V
		–	–	500	–	–	500		V_{CC} = 4.5 V
		–	–	400	–	–	–		V_{CC} = 6.0 V

ABSOLUTE MAXIMUM RATINGS

Limiting values is accordance with the Absolute Maximum Rating System (IEC 134).
Voltages are referenced to GND (ground = 0 V)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	DC supply voltage		–0.5	+7.0	V
$\pm I_{IK}$	DC input diode current	$V_I < -0.5$ or $V_I > V_{CC} + 0.5$ V	–	20	mA
$\pm I_{OK}$	DCoutput diode current	$V_O < -0.5$ or $V_O > V_{CC} + 0.5$ V	–	20	mA
$\pm I_O$	DC output source or sink current bus driver outputs	$-0.5V < V_O < V_{CC} + 0.5$ V	–	35.0	mA
$\pm I_{CC}$	DC V_{CC} or GND current for types with bus driver outputs		–	70	mA
T_{stg}	storage temperature range		–65	+150	°C
P_D	power dissipation per package 5 pins plastic SC88A	for temperature range: – 40 to + 125 °C above +55 °C derate linearly with 2.5 mW/K	–	200	mW

Notes

1. Stresses beyond those listed may cause permanent damage to the device. These are stress rating only and functional operation of the device at these or any other conditions beyond those under ‘recommended operating conditions’ is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.
2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

DC CHARACTERISTICS FOR THE 74HC1G

Over recommended operating conditions.
Voltage are referenced to GND (ground = 0 V)

SYMBOL	PARAMETER	T_{amb} (°C)					UNIT	TEST CONDITIONS	
		–40 to +85			–40 to +125			V_{CC} (V)	OTHER
		MIN.	TYP.(1)	MAX.	MIN.	MAX.			
V_{IH}	HIGH level input voltage	1.5	1.2	–	1.5	–	V	2.0	
		3.15	2.4	–	3.15	–		4.5	
		4.2	3.2	–	4.2	–		6.0	
V_{IL}	LOW level input voltage	–	0.8	0.5	–	0.5	V	2.0	
		–	2.1	1.35	–	1.35		4.5	
		–	2.8	1.8	–	1.8		6.0	
V_{OH}	HIGH level output voltage; all outputs	1.9	2.0	–	1.9	–	V	2.0	$V_I = V_{IH}$ or V_{IL}, $-I_O = 20\ \mu A$
		4.4	4.5	–	4.4	–		4.5	
		5.9	6.0	–	5.9	–		6.0	
V_{OH}	HIGH level output voltage; Bus driver outputs	3.84	4.32	–	3.7	–	V	4.5	$V_I = V_{IH}$ or V_{IL}, $-I_O = 6.0$ mA
		5.34	5.81	–	5.2	–		6.0	$V_I = V_{IH}$ or V_{IL}, $-I_O = 7.8$ mA
V_{OL}	LOW level output voltage; all outputs	–	0	0.1	–	0.1	V	2.0	$V_I = V_{IH}$ or V_{IL}, $I_O = 20\ \mu A$
		–	0	0.1	–	0.1		4.5	
		–	0	0.1	–	0.1		6.0	
V_{OL}	LOW level output voltage; Bus driver outputs	–	0.15	0.33	–	0.4	V	4.5	$V_I = V_{IH}$ or V_{IL}, $I_O = 6.0$ mA
		–	0.16	0.33	–	0.4		6.0	$V_I = V_{IH}$ or V_{IL}, $I_O = 7.8$ mA
I_I	input leakage current	–	–	1.0	–	1.0	µA	6.0	$V_I = V_{CC}$ or GND
I_{OZ}	3-state output OFF-state current	–	–	5	–	10	µA	6.0	$V_I = V_{IH}$ or V_{IL}, $V_O = V_{CC}$ or GND
I_{CC}	Quiescent supply current	–	–	10	–	20	µA	6.0	$V_I = V_{CC}$ or GND, $I_O = 0$

Note

1. All typical values are measured at $T_{amb} = 25$ °C.

DC CHARACTERISTICS FOR THE 74HCT1G

Over recommended operating conditions.
Voltage are referenced to GND (ground = 0 V.)

SYMBOL	PARAMETER	T_{amb} (°C)					UNIT	TEST CONDITIONS	
		–40 to +85			–40 to +125			V_{CC} (V)	OTHER
		MIN.	TYP.(1)	MAX.	MIN.	MAX.			
V_{IH}	HIGH level input voltage	2.0	1.6	–	2.0	–	V	4.5 to 5.5	
V_{IL}	LOW level input voltage	–	1.2	0.8	–	0.8	V	4.5 to 5.5	
V_{OH}	HIGH level output voltage; all outputs	4.4	4.5	–	4.4	–	V	4.5	$V_I = V_{IH}$ or V_{IL}, $-I_O = 20$ μA
V_{OH}	HIGH level output voltage; Bus driver outputs	3.84	4.32	–	3.7	–	V	4.5	$V_I = V_{IH}$ or V_{IL}, $-I_O = 6.0$ mA
V_{OL}	LOW level output voltage; all outputs	–	0	0.1	–	0.1	V	4.5	$V_I = V_{IH}$ or V_{IL}, $I_O = 20$ μA
V_{OL}	LOW level output voltage; Bus driver outputs	–	0.16	0.33	–	0.4	V	4.5	$V_I = V_{IH}$ or V_{IL}, $I_O = 6.0$ mA
I_I	input leakage current	–	–	1.0	–	1.0	μA	5.5	$V_I = V_{CC}$ or GND
I_{OZ}	3-state output OFF-state current	–	–	5	–	10	μA	5.5	$V_I = V_{IH}$ or V_{IL}, $V_O = V_{CC}$ or GND
I_{CC}	Quiescent supply current	–	–	10	–	20	μA	5.5	$V_I = V_{CC}$ or GND, $I_O = 0$
ΔI_{CC}	Additional supply current per input	–	–	500	–	850	μA	4.5 to 5.5	$V_I = V_{CC} - 2.1$, $I_O = 0$

Note

1. All typical values are measured at $T_{amb} = 25$ °C.

AC CHARACTERISTICS FOR 74HC1G126

GND = 0 V; $t_r = t_f \leq 6.0$ ns; CL = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)					UNIT	TEST CONDITIONS	
		–40 to +85			–40 to +125			V_{CC} (V)	WAVEFORMS
		MIN.	TYP.(1)	MAX.	MIN.	MAX.			
t_{PHL}/t_{PLH}	propagation delay inA to outY	–	24	125	–	150	ns	2.0	see Fig.5 and Fig.7
		–	10	25	–	30		4.5	
		–	9	21	–	26		6.0	
t_{PZH}/t_{PZL}	3-state output enable time OE to outY	–	24	155	–	190	ns	2.0	see Fig.6 and Fig.7
		–	10	31	–	38		4.5	
		–	8	26	–	32		6.0	
t_{PHZ}/t_{PLZ}	3-state output disable time OE to outY	–	16	155	–	190	ns	2.0	see Fig.6 and Fig.7
		–	12	31	–	38		4.5	
		–	11	26	–	32		6.0	

Note

1. All typical values are measured at T_{amb} = 25 °C.

AC CHARACTERISTICS FOR 74HCT1G126

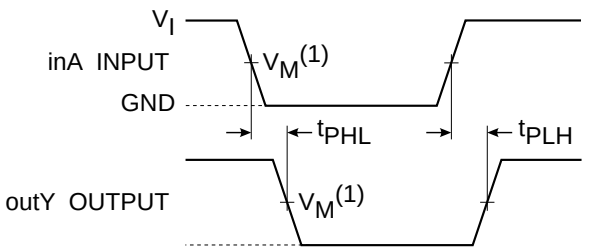
GND = 0 V; $t_r = t_f \leq 6.0$ ns; CL = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)					UNIT	TEST CONDITIONS	
		–40 to +85			–40 to +125			V_{CC}(V)	WAVEFORMS
		MIN.	TYP.(1)	MAX.	MIN.	MAX.			
t_{PHL}/t_{PLH}	propagation delay inA to outY	–	11	30	–	36	ns	4.5	see Fig.5 and Fig.7
t_{PZH}/t_{PZL}	3-state output enable time OE to outY	–	10	35	–	42	ns	4.5	see Fig.6 and Fig.7
t_{PHZ}/t_{PLZ}	3-state output disable time OE to outY	–	12	31	–	38	ns	4.5	see Fig.6 and Fig.7

Note

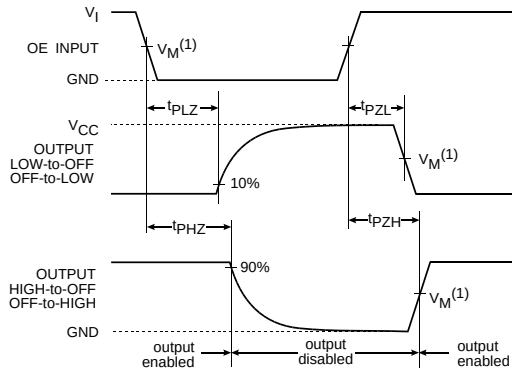
1. All typical values are measured at T_{amb} = 25 °C.

AC WAVEFORMS



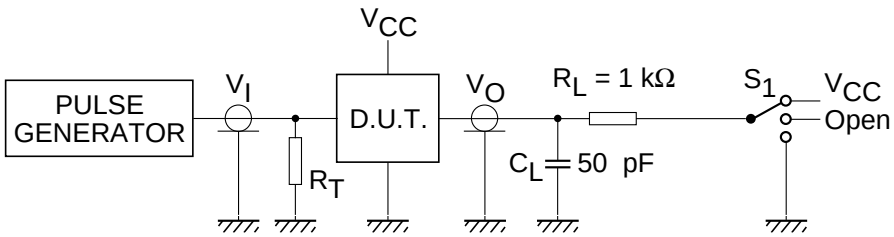
(1) HC1G V_M = 50 %; V_I = GND to V_{CC}
HCT1G V_M = 1.3 V; V_I = GND to 3.0 V

Fig.5 The input (inA) to output (outY) propagation delays.



(1) HC1G V_M = 50 %; V_I = GND to V_{CC}
HCT1G V_M = 1.3 V; V_I = GND to 3.0 V

Fig.6 The 3-state enable and disable times.



Definitions for test circuit ;

C_L = Load capacitance including jig and probe capacitance (See AC Characteristics for values).

R_L = Load resistance.(See AC Characteristics for values).

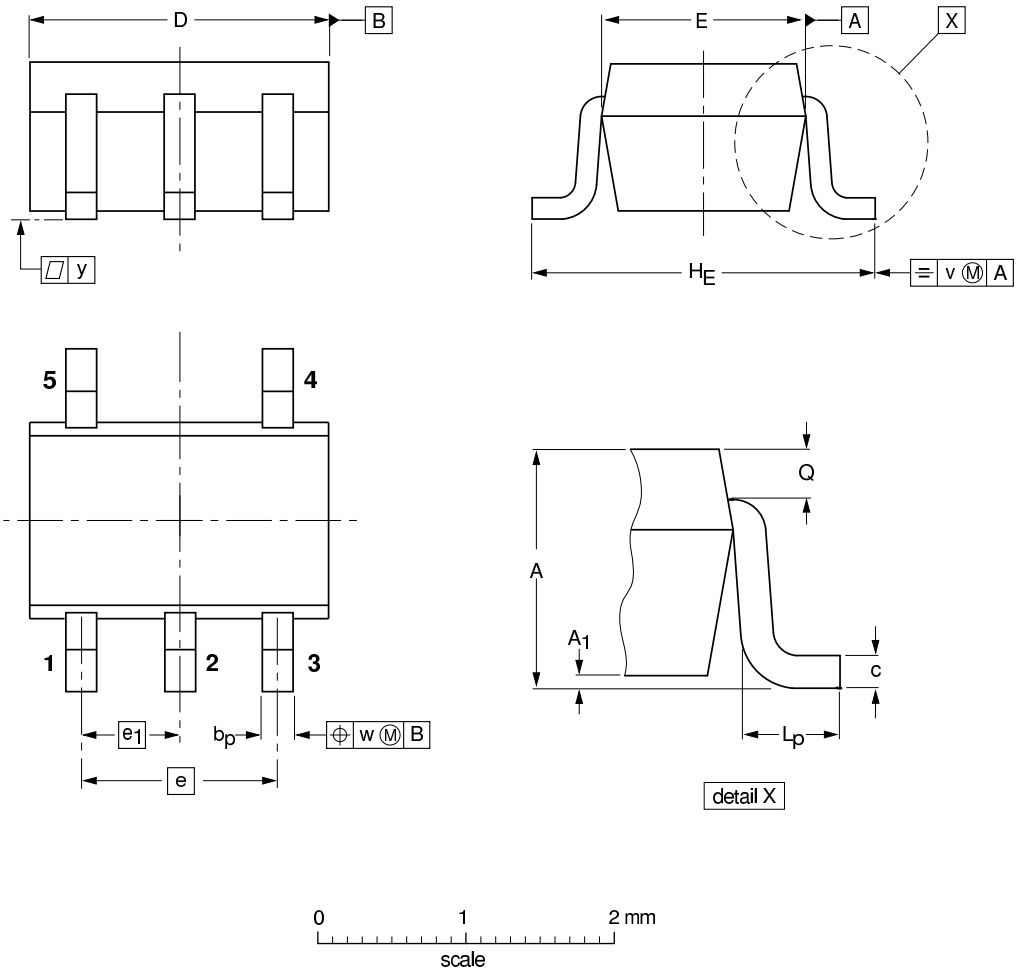
R_T = Termination resistance should be equal to the output impedance Zo of the pulse generator.

Test	S_1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND

Fig.7 Load circuitry for switching times.

PACKAGE OUTLINES

Plastic surface mounted package; 5 leads **SOT353**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E (2)	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT353			SC-88A			97-02-28

SOLDERING

Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

Reflow soldering

Reflow soldering techniques are suitable for all SO packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

Wave soldering

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Repairing soldered joints

Fix the component by first soldering two diagonally- opposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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